



## CVD graphene synthesis, fabrication & characterization for applications

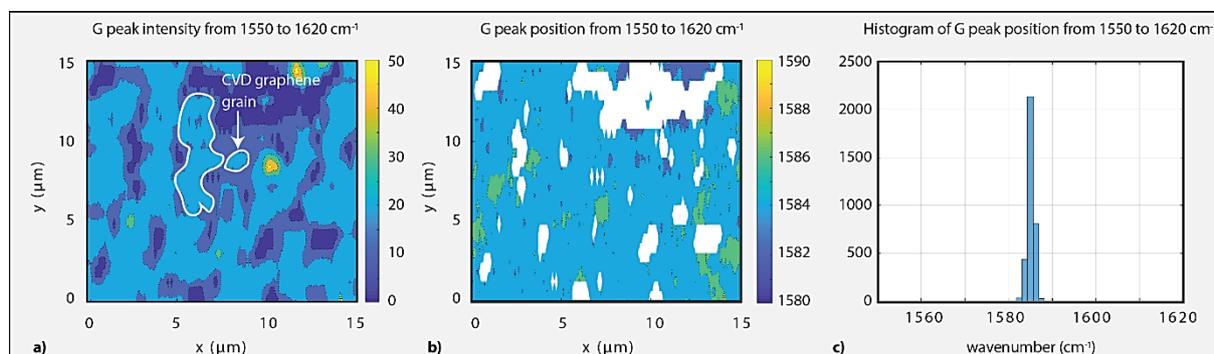
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### Abstract

Single layer graphene (SLG) films offer several features such as i) a wide range of non-covalent molecular functionalization<sup>[1]</sup>, ii) high field effect mobility & current density ( $\sim 6 \times 10^3 \text{ cm}^2/\text{Vs}$ , 300 K)<sup>[2, 3]</sup>, iii) transparency ( $\sim 97\%$  to visible light), iv) flexibility & high mechanical strength ( $\sim 1 \text{ TPa}$ ). Using chemical vapor deposition (CVD), mass-production of graphene films for industrial applications is achievable today. Current progress in standardization of graphene & 2D material quality is encouraging towards industrial applications using graphene films such as low-cost diagnostic kits.<sup>[4]</sup> In this poster, we present the progress in CVD graphene synthesis and film quality characterization (see: figure 1) using Raman spectroscopy. Second, functionalization of the graphene surface using two types of molecular linkers is performed to assess potential applications of graphene films. Third, a novel approach for CVD heterostructure formation using CVD graphene & CVD hexagonal Boron Nitride (hBN) is presented. Such heterostructure are explored for the development of high performance graphene device applications<sup>[5]</sup>.



**Figure 1.** CVD graphene grain quality characterization using confocal Raman spectroscopy. Inset: white line & arrow indicating the presence of graphene grain. **a)** Map of the G peak intensity (area:  $15 \times 15 \mu\text{m}^2$ ), **b)** G peak position & **c)** Histogram of peak position. **Note:** In figure b, the graphene grain regions are isolated from the substrate ( $\text{SiO}_2/\text{Si}$ ) using image processing.

### References

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